

# 5DS03B

## Switching Diode



### Features

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- High – speed

Item	Characteristics
Wafer size	5inch
Chip size	235*235um

### Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V <sub>RSM</sub>	100	V
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	75	V
Repetitive Peak Forward Current	I <sub>FRM</sub>	500	mA
Continuous Forward Current	I <sub>O</sub>	150	mA
Non-Repetitive Peak Forward Current @t=1us	I <sub>FSM</sub>	2	A
Power Dissipation	P <sub>D</sub>	500	mW
Junction Temperature	T <sub>j</sub>	175	degC
Storage Temperature	T <sub>stg</sub>	-65to+175	degC

### Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V <sub>F</sub>		1.05	V	I <sub>F</sub> =100mA
Breakdown Voltage	V <sub>B</sub>	100		V	I <sub>R</sub> =100uA
Reverse Current	I <sub>R</sub>		25	nA	V <sub>R</sub> =20V
Junction Capacitance	C <sub>T</sub>		4	pF	V <sub>R</sub> =0V, f=1MHz
Reverse Recovery Time	t <sub>rr</sub>		4	nsec	I <sub>F</sub> =I <sub>R</sub> =10mA R <sub>L</sub> =100Ω, i <sub>rr</sub> =1mA

### Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
V <sub>F</sub>		1.05	V	I <sub>F</sub> =100mA
V <sub>B</sub>	105		V	I <sub>R</sub> =100uA
I <sub>R1</sub>		25	nA	V <sub>R</sub> =30V
I <sub>R2</sub>		2	uA	V <sub>R</sub> =85V
C <sub>T</sub>		4	pF	V <sub>R</sub> =0V, f=1MHz
t <sub>rr</sub>		4	nsec	I <sub>F</sub> =I <sub>R</sub> =10mA R <sub>L</sub> =100Ω, i <sub>rr</sub> =1mA

**Note** Equivalent type : BAW62

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